

# MICROWAVE DIODE CORPORATION



## IN830 IN830A

## SILICON UHF DETECTOR DIODE

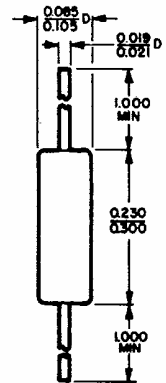
The IN830 and IN830A are point contact barrier diodes used in signal detection. While Tangential Sensitivity is not specified in this instance, the diodes possess a minimum of -40 dbm up to 3 GHz.

Electrical Characteristics at  $T = 25^\circ$

Burnout CW, 375 mw  
Peak @ 1 us 15w  
Typical .3pf  $C_{jo}$

IN830 Detector rectification efficiency = 65% minimum at  $f = 100$  mc

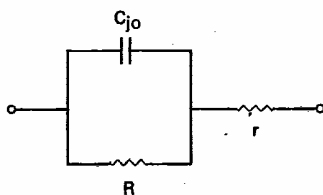
IN830A PIV = 5 volts minimum.



### PACKAGE OUTLINE

**FIGURE 1**

DIODE Equivalent Circuit



R = Series resistance  
r = Spreading resistance  
 $C_{jo}$  = Junction Capacitance

# MICROWAVE DIODE CORPORATION

U.S. ROUTE 3 · BOX 250  
WEST STEWARTSTOWN, NEW HAMPSHIRE 03597  
(603) 246-3362

